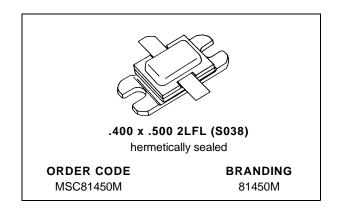


MSC81450M

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

- REFRACTORY\GOLD METALLIZATION
- RUGGEDIZED VSWR 25:1
- INTERNAL INPUT/OUTPUT MATCHING
- LOW THERMAL RESISTANCE
- METAL/CERAMIC HERMETIC PACKAGE
- P_{OUT} = 450 W MIN. WITH 7.0 dB GAIN

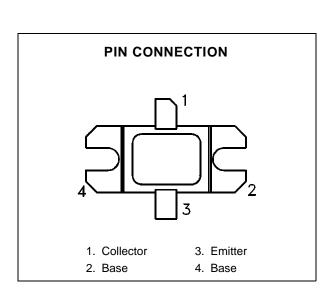


DESCRIPTION

The MSC81450M device is a high power pulsed transistor specifically designed for IFF avionics applications.

This device is capable of withstanding a minimum 25:1 load mismatch at any phase angle under full rated conditions.

The MSC81450M is housed in the unique BIG-PACTM package with internal input/output matching structures.



ABSOLUTE MAXIMUM RATINGS $(T_{case} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation*	910	W
Ic	Device Current*	28	А
Vcc	Collector-Supply Voltage*	55	V
TJ	Junction Temperature (Pulsed RF Operation)	250	°C
T _{STG}	Storage Temperature	- 65 to +200	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance*	0.15	°C/W
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^{*}Applies only to rated RF amplifier operation

April 7, 1995

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

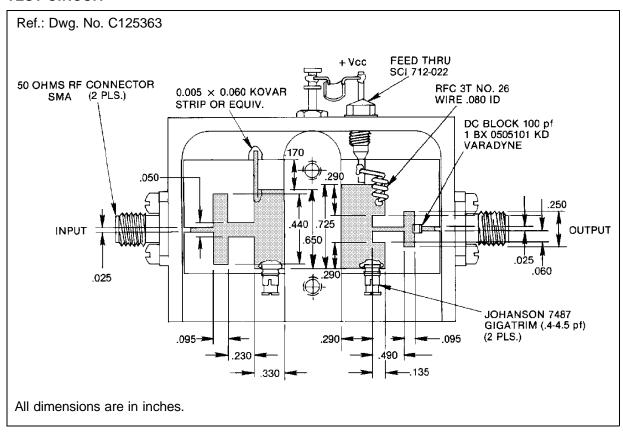
Symbol	Test Conditions	Value			11:4		
		Min.	Тур.	Max.	Unit		
BV _{CBO}	$I_C = 15mA$	$I_{E} = 0mA$		65	_	_	V
BV _{EBO}	$I_E = 1mA$	$I_C = 0mA$		3.5	_	_	V
BVCER	$I_C = 50 \text{mA}$	$R_{BE} = 10\Omega$		65			V
I _{CES}	V _{CE} = 50V			_	_	35	mA
h _{FE}	V _{CE} = 5V	$I_C = 1A$		15	_	120	_

DYNAMIC

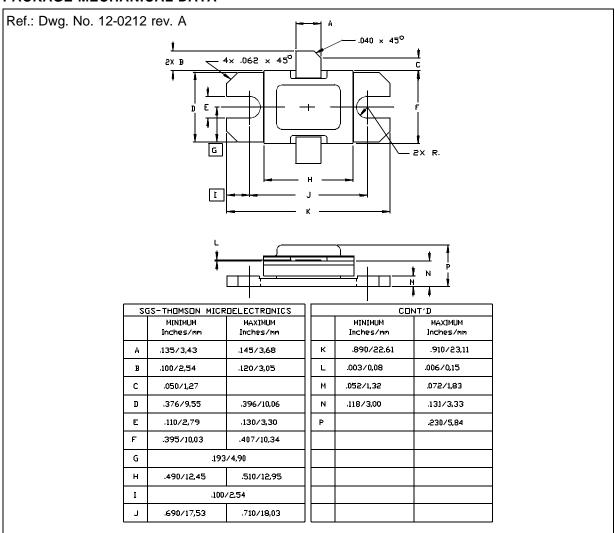
Symbol	Test Conditions		Value			l lmi4	
Symbol	rest conditions			Min.	Тур.	Max.	Unit
Pout	f = 1090 MHz	$P_{IN} = 90 \text{ W}$	$V_{CC} = 50 \text{ V}$	450	500	_	W
ης	f = 1090 MHz	P _{IN} = 90 W	V _C C = 50 V	40	_	_	%
G _P	f = 1090 MHz	P _{IN} = 90 W	Vcc = 50 V	7.0		_	dB

Note: Pulse Width = 10μ Sec Duty Cycle = 1%

TEST CIRCUIT



PACKAGE MECHANICAL DATA



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